CLAIMS

1. A ceramic substrate for apparatuses for use in semiconductor manufacture and/or inspection,

wherein the level of α-rays radiated from said ceramic substrate exceeds 0.25 $c/cm^2 \cdot hr$ and is not higher than 50 $c/cm^2 \cdot hr$.

2. The ceramic substrate according to claim 1,

wherein said ceramic substrate has a temperature adjusting means.

3. A ceramic heater, for heating a semiconductor, comprising a ceramic substrate and a heating element disposed on the surface or internally thereof,

wherein the level of α-rays radiated from said ceramic substrate exceeds 0.25 $c/cm^2 \cdot hr$ and is not higher than 50 $c/cm^2 \cdot hr$.

4. An electrostatic chuck comprising a ceramic substrate and electrodes embedded therein,

wherein the level of α-rays radiated from said ceramic substrate exceeds 0.25 $c/cm^2 \cdot hr$ and is not higher than 50 $c/cm^2 \cdot hr$.

5. The electrostatic chuck according to claim 4,

wherein said ceramic substrate has a temperature adjusting means.

6. A substrate for a wafer prober comprising a ceramic substrate and a conductor layer formed on the surface thereof,

wherein the level of α-rays radiated from the surface of said ceramic substrate exceeds 0.25 $c/cm^2 \cdot hr$ and is not higher than 50 $c/cm^2 \cdot hr$.

7. The substrate for a wafer prober according to claim 6,

wherein said ceramic substrate has a temperature adjusting

means.